PNP SILICON POWER TRANSISTOR

...designed for output stage of 3 watts audio amplifier, voltage regulator, DC-DC converter and relay driver.

MAXIMUM RATINGS (Ta = 25 °C)

Characteristic	Symbol	Value	Unit
Collector Base Voltage	Vсво	-40	V
Collector Emitter Voltage	VCEO	-30	V
Emitter Base Voltage	Vebo	-5	V
Collector Current (DC)	IC(DC)	-3	А
Collector Current (Pulse)	IC(Pulse)*	-7	А
Total Power Dissipation	Ptot		W
Ta=25°C		1	
Tc=25°C		10	
Storage Temperature	Tstg	-55 ~ 150	°C
Junction Temperature	Tj	150	°C

*Pulse Test PW $\leq 350 \mu s,$ Duty Cycle $\leq 2\%$



ELECTRICAL CHARACTERISTICS (Ta = 25 °C)

Characteristic	Symbol	Test Condition	Min.	Тур.	Max.	Unit
Collector Cutoff Current	Ісво	VCB =-30V, IE =0	-	-	-1	μA
Emitter Cutoff Current	Іево	VEB =-3.0V, IC =0	-	-	-1	μA
Collector Saturation Voltage	VCE(sat)	Ic =-2.0A, IB =-0.2A**	-	-0.3	-0.5	V
Base Saturation Voltage	VBE(sat)	Ic =-2.0A, IB =-0.2A**	-	-1	-2	V
DC Current Gain	hFE1	Vce=-2.0V, Ic=-20mA**	30	220	-	-
DC Current Gain	hFE2	VCE =-2.0V, IC =-1.0A**	60	160	400	-
Gain Bandwidth Product	f⊤	VCE =-50V, IC =-0.1A	-	80	-	MHz
Output Capacitance	Cob	VCB =-10V, IE =0, f=1.0MHz	-	55	-	pF

**Pulse Test: PW $\leq 350 \mu s,$ Duty Cycle $\leq 2\%$

Classification of hFE(2)

Class	R	Q	Р	E
hFE(2)	60 to 120	100 to 200	160 to 320	200 to 400

PMC reserves the right to make changes without further notice to any products herein. **PMC** makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does **PMC** assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation consequential damages. The examples of applied circuits are provided as reference to the reader therefore we shall not undertake any responsibility for the exercise of rights by third parties.

© PMC Components Pte Ltd., Singapore, 2000

PNP SILICON POWER TRANSISTOR

